

Radar Pulsed Power Transistor 80W, 1.2-1.4 GHz, 150µs Pulse, 10% Duty

M/A-COM Products Released, 30 May 07

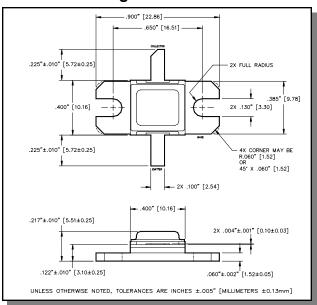
Features

- · NPN silicon microwave power transistors
- · Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	70	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ic	6.4	Α
Power Dissipation @ +25°C	P _{TOT}	220	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 35mA		BV_CES	70	-	V
Collector-Emitter Leakage Current	V _{CE} = 40V		I _{CES}	-	3.5	mA
Thermal Resistance	Vcc = 40V, Pin = 13W	F = 1.2, 1.3, 1.4 GHz	R _{TH(JC)}	-	0.8	°C/W
Output Power	Vcc = 40V, Pin = 13W	F = 1.2, 1.3, 1.4 GHz	P _{OUT}	80	=	W
Power Gain	Vcc = 40V, Pin = 13W	F = 1.2, 1.3, 1.4 GHz	G _P	7.9	=	dB
Collector Efficiency	Vcc = 40V, Pin = 13W	F = 1.2, 1.3, 1.4 GHz	ης	50	-	%
Input Return Loss	Vcc = 40V, Pin = 13W	F = 1.2, 1.3, 1.4 GHz	RL	-	-9	dB
Load Mismatch Tolerance	Vcc = 40V, Pin = 13W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	3:1	-
Load Mismatch Stability	Vcc = 40V, Pin = 13W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

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 Visit www.macomtech.com for additional data sheets and product information.

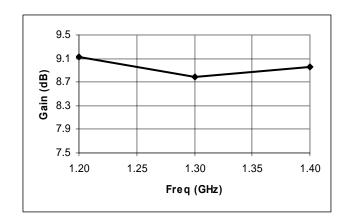


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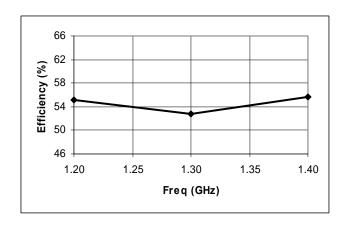
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
1.2	13	106	9.13	4.83	55.1	-15.4	S	Р
1.3	13	98	8.78	4.66	52.7	-15.5	S	Р
1.4	13	102	8.96	4.61	55.6	-14.9	S	Р

Gain vs. Frequency

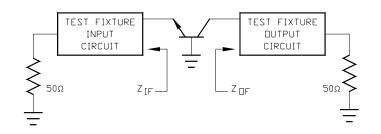


Collector Efficiency vs. Frequency



RF Test Fixture Impedance

F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)		
1.2	9.4 - j4.5	7.0 - j2.8		
1.3	8.3 - j2.8	4.5 - j3.2		
1.4	7.9 - j1.3	3.0 + j2.1		



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